

TOSHIBA HIGH EFFICIENCY RECTIFIER (HED) SILICON EPITAXIAL JUNCTION TYPE

1DL42A

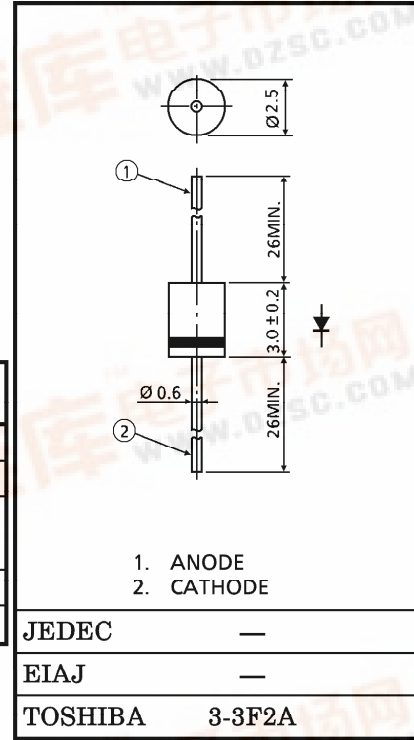
SWITCHING TYPE POWER SUPPLY APPLICATIONS

Unit in mm

- Repetitive Peak Reverse Voltage : $V_{RRM}=200V$
- Average Forward Current : $I_F(AV)=1.0A$
- Very Fast Reverse-Recovery Time : $t_{rr}=35ns$ (Max.)
- Low Forward Voltage : $V_{FM}=0.98V$ (Max.)
- Available to Reduce Switching Losses and Output Noise.

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	200	V
Average Forward Current	$I_F(AV)$	1.0	A
Peak One Cycle Surge Forward Current (Non-Repetitive)	I_{FSM}	30 (50Hz) 33 (60Hz)	A
Junction Temperature	T_j	-40~150	°C
Storage Temperature Range	T_{stg}	-40~150	°C



Weight : 0.18g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	V_{FM}	$I_{FM}=1.0A$	—	—	0.98	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM}=200V$	—	—	100	μA
Reverse Recovery Time	t_{rr}	$I_F=1A, di/dt=-30A/\mu s$	—	—	35	ns
Forward Recovery Time	t_{fr}	$I_F=1.0A$	—	—	100	ns

MARKING

